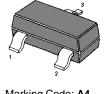
1SS184 Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance





Marking Code: **A4** SOT-23 Plastic Package

Applications

• Ultra high speed switching application

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current	I _{F(AV)}	100	mA
Maximum Peak Forward Current	I _{FM}	300	mA
Non-repetitive Peak Forward Surge Current (10 ms)	I _{FSM}	2	А
Power Dissipation	P _{tot}	350	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at Ta = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at $V_R = 30 \text{ V}$ at $V_R = 80 \text{ V}$	I _R	0.1 0.5	μА
Total Capacitance at $V_R = 0$, $f = 1$ MHz	Ст	3	pF
Reverse Recovery Time at I _F = 10 mA	t _{rr}	4	ns

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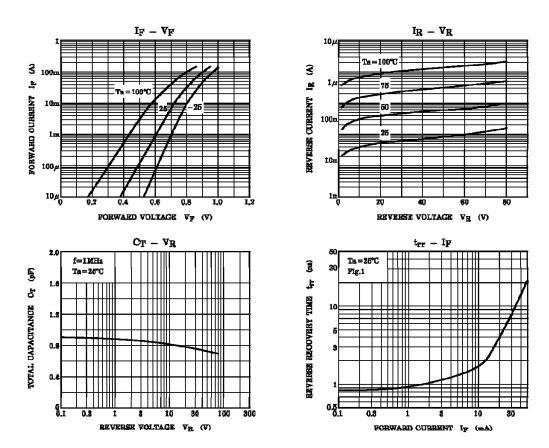
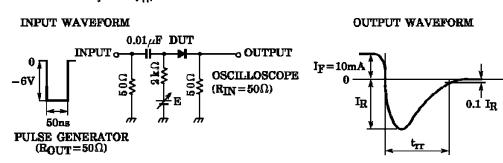


Fig.1 Reverse recovery time (t_{rr}) test circuit

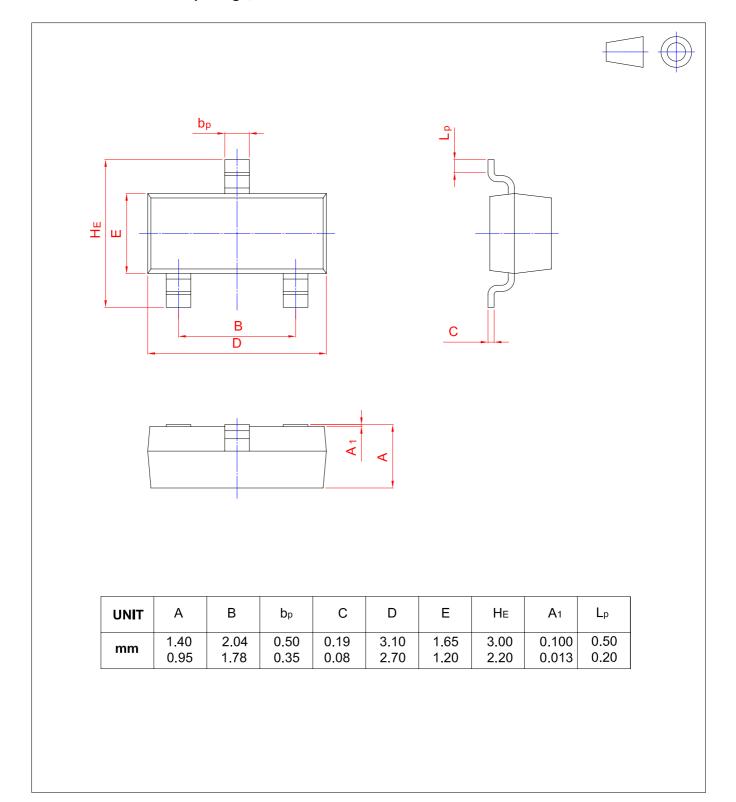


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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



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